

**P-Channel MOSFET** 

### **General Description**

The WSK92P06 is the highest performance trench P-ch MOSFETs with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSK92P06 meet the RoHS and Green Product requirement , 100% EAS guaranteed with full function reliability approved.

#### Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

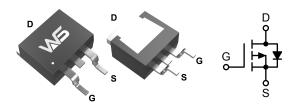
### **Product Summery**

BV <sub>DSS</sub>	R <sub>DSON</sub>	I <sub>D</sub>
-60V	10mΩ	-90A

#### Applications

- Power Management
- Load Switch

#### **TO-263-2L Pin Configuration**



### **Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	-60	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>C</sub> =25℃	Continuous Drain Current, -V <sub>GS</sub> @ -10V	-90	A
I <sub>D</sub> @T <sub>C</sub> =100℃	Continuous Drain Current, -V <sub>GS</sub> @ -10V	-40	A
I <sub>DM</sub>	Pulsed Drain Current	-190	А
P <sub>D</sub> @T <sub>C</sub> =25℃	Total Power Dissipation	96	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range -55 to 1		°C

#### **Thermal Data**

Symbol	Parameter	Тур.	Max.	Unit
R <sub>eja</sub>	Thermal Resistance Junction-Ambient		62	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case		1.3	°C/W



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### Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =-250uA	-60			V	
Р	Static Drain-Source On-Resistance	V <sub>GS</sub> =-10V , I <sub>D</sub> =-18A		10	14	<b>m</b> 0	
R <sub>DS(ON)</sub>	Static Drain-Source Off-Resistance	V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-12A		13	18	18 mΩ	
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS}$ = $V_{DS}$ , $I_D$ =-250 $uA$	-1.1	-1.8	-2.5	V	
I <sub>DSS</sub>	Drain-Source Leakage Current	$V_{\text{DS}}\text{=-48V}$ , $V_{\text{GS}}\text{=}0\text{V}$ , $T_{\text{J}}\text{=}25^\circ\!\mathrm{C}$			1	uA	
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}=\pm 20V$ , $V_{DS}=0V$			±100	nA	
Qg	Total Gate Charge	VDS = -30 V, VGS = -10 V,		89			
Q <sub>gs</sub>	Gate-Source Charge	$D_{S} = -30 \text{ V}, \text{ VGS} = -10 \text{ V},$		12		nC	
Q <sub>gd</sub>	Gate-Drain Charge	ID=-17A		32			
T <sub>d(on)</sub>	Turn-On Delay Time	Vdd = -30 V,		15			
Tr	Rise Time	$R_L = 30\Omega$ , $I_D = -1 A$ ,		13			
T <sub>d(off)</sub>	Turn-Off Delay Time	$V_{\text{GEN}} = -10 \text{ V}, \text{ Rg} = 6\Omega$		110		ns	
T <sub>f</sub>	Fall Time			60			
C <sub>iss</sub>	Input Capacitance			4066			
Coss	Output Capacitance	VDS=-30V,VGS=0V, f=1.0MHz		501		pF	
C <sub>rss</sub>	Reverse Transfer Capacitance			291			

### **Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current	T <sub>C</sub> =25 <sup>°</sup> C			-40	А
V <sub>SD</sub>	Diode Forward Voltage	$V_{GS}$ =0V , $I_{S}$ =-1A , $T_{J}$ =25 $^{\circ}$ C			-1.2	V

A: The value of R e JA is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with TA=25C. The value in any given

application depends on the user's specific board design.

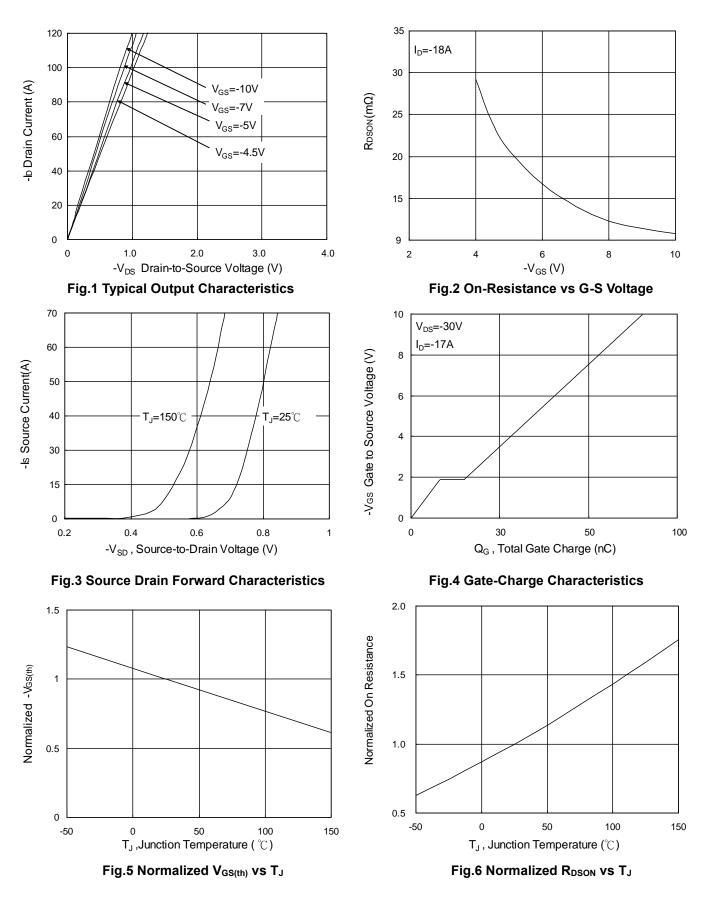
B: Repetitive rating, pulse width limited by junction temperature.

C: The current rating is based on the t≤ 10s junction to ambient thermal resistance rating.



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## **Typical Characteristics**





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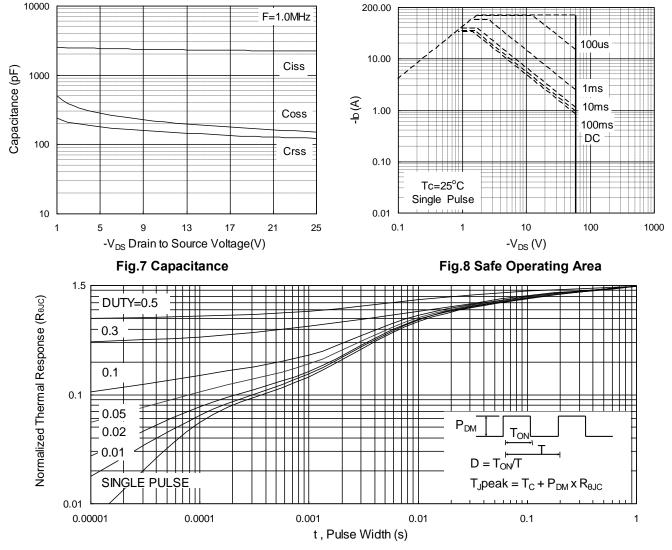
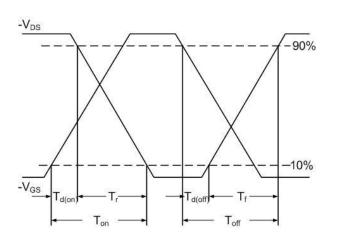


Fig.9 Normalized Maximum Transient Thermal Impedance





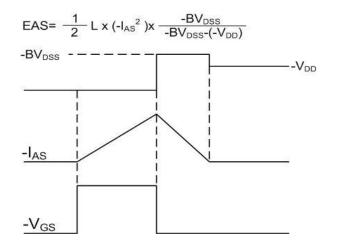
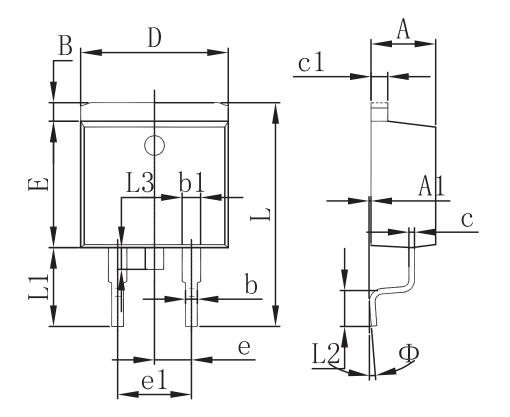


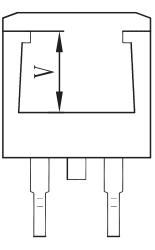
Fig.11 Unclamped Inductive Waveform



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# Packaging information





Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	4.470	4.670	0.176	0.184	
A1	0.000	0.150	0.000	0.006	
В	1.120	1.420	0.044	0.056	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.310	0.530	0.012	0.021	
c1	1.170	1.370	0.046	0.054	
D	10.010	10.310	0.394	0.406	
E	8.500	8.900	0.335	0.350	
е	2.540	TYP.	0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
L	14.940	15.500	0.588	0.610	
L1	4.950	5.450	0.195	0.215	
L2	2.340	2.740	0.092	0.108	
L3	1.300	1.700	0.051	0.067	
Φ	0°	8°	0°	8°	
V	5.600	REF.	0.220REF.		



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